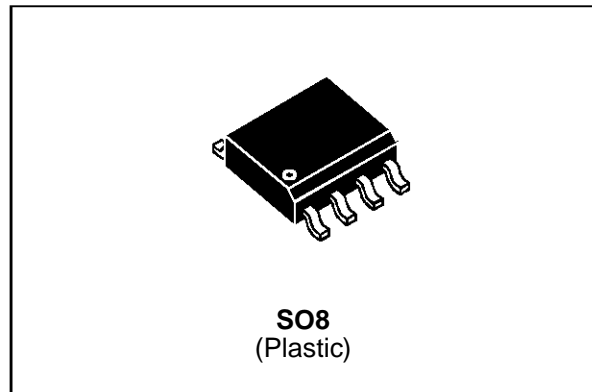


Application Specific Discretes **UNIDIRECTIONAL TRANSIENT SUPPRESSOR**
A.S.D.TM **PROGRAMMED BY VOLTAGE & CURRENT**

FEATURES AND BENEFITS

- UNIDIRECTIONAL OVERVOLTAGE SUPPRESSOR PROGRAMMED BY VOLTAGE AND CURRENT: CROWBAR OCCURS AT THE DESIRED LEVEL.
- MULTI-LINE PROTECTION MODE : ONE DEVICE CAN PROTECT SEVERAL LINES, ENABLING SPACE SAVING ON THE BOARD.
- HIGH CURRENT CAPABILITY :
I_{PP} = 100A for 10/1000µs,
ENSURING AN EXCELLENT PROTECTION AGAINST HIGH ENERGY TRANSIENTS.



DESCRIPTION

Dedicated to sensitive telecom equipment protection, the LCP3121 provides protection which can be programmed by both voltage and current.

The breakdown voltage can be easily programmed by using an external zener diode.

The protection function programmed by the current is achieved with the use of a resistor between the gate and the cathode. The value of the resistor will determine the level of the desired current before the triggering of the device.

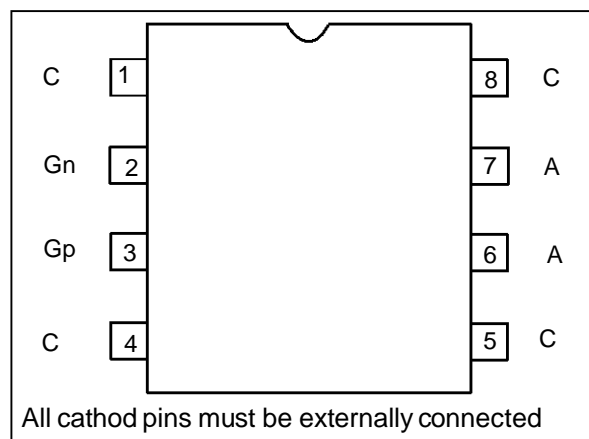
A multiple protection mode is also performed when using several diodes providing each line interface with an optimized protection level.

If desired, a bidirectional protection function can be achieved by the use of two LCP3121.

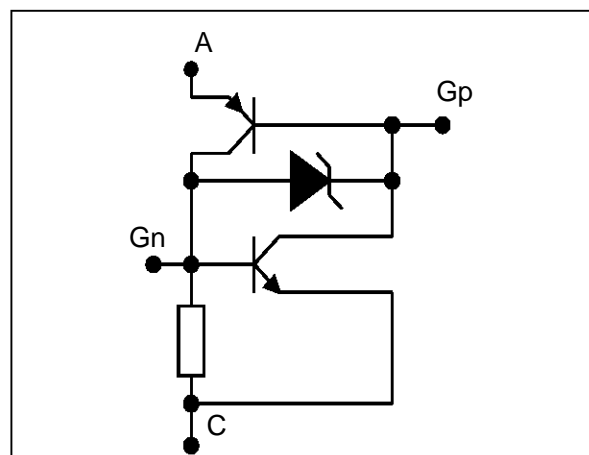
COMPLIES WITH FOLLOWING STANDARDS :

CCITT K20 :	10/700µs	1.5kV
	5/310µs	
VDE 0433 :	10/700µs	2kV
	5/310µs	
VDE 0878 :	1.2/50µs	1.5kV
	1/20µs	
FCC part 68 :	2/10µs	2.5kV
BELLCORE		
TR-NWT-001089 :	2/10µs	

PIN-OUT CONFIGURATION



FUNCTIONAL DIAGRAM



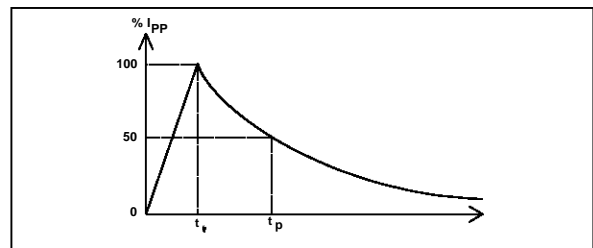
LCP3121

ABSOLUTE MAXIMUM RATINGS ($T_{amb} = 25^{\circ}\text{C}$)

Symbol	Parameter	Value	Unit
I_{PP}	Peak pulse current (see note 1)	10/1000 μs	A
I_{TSM}	Non repetitive surge peak on-state current (F = 50 Hz)	$t_p = 10\text{ms}$ $t_p = 1\text{s}$	A
V_{AC} V_{GA}	Maximum voltage between A and C Maximum voltage between G (Gn or Gp) and A	100 80	V
T_{stg} T_j	Storage temperature range Maximum junction temperature	- 40 to + 150 150	$^{\circ}\text{C}$

Note 1 : Pulse waveform :

10/1000 μs $t_r=10\mu\text{s}$ $t_p=1000\mu\text{s}$



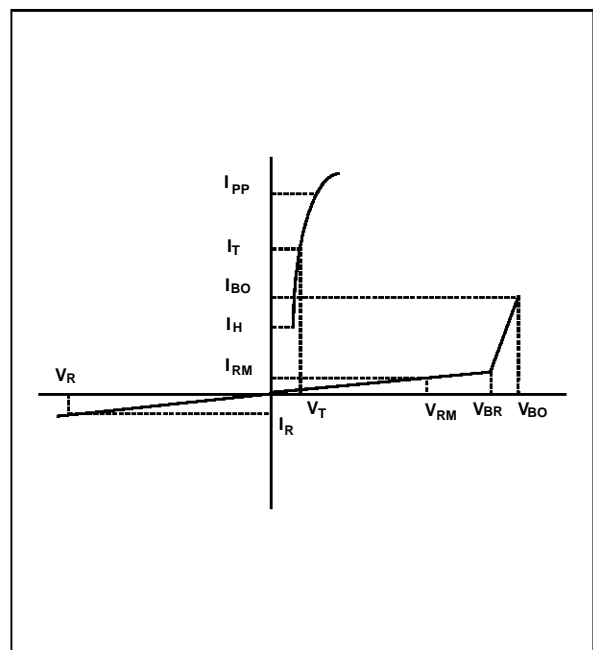
THERMAL RESISTANCE

Symbol	Parameter	Value	Unit
$R_{th(j-a)}$	Junction to ambient (on board)	170	$^{\circ}\text{C/W}$

ELECTRICAL CHARACTERISTICS

($T_{amb} = 25^{\circ}\text{C}$, unless otherwise specified)

Symbol	Parameter
V_{RM}	Stand-off voltage
V_{BR}	Breakdown voltage
V_{BO}	Breakover voltage
I_H	Holding current
V_T	On-state voltage
I_{BO}	Breakover current
I_{RM}	Leakage current at V_{RM}
I_R	Leakage current at V_R
I_{PP}	Peak pulse current
V_R	Maximum reverse voltage
C_{off}	Off-state capacitance
V_G	Gate voltage
I_{GP}	Gp triggering current
I_{GN}	Gn triggering current



OPERATION WITHOUT GATES

Symbol	Test conditions	Min.	Max.	Unit
I_{RM}	$V_{RM} = 60V$ $V_{RM} = 90V$		5 8	μA
I_R	at $V_R = 180V$		50	μA
V_{BR}	at 1mA	100		V
I_{BO}		80	500	mA
V_{BO}	Measured at 50Hz		180	V
V_T	Square pulse; $t_p=500\mu s$; $I_T=1A$		3	V
I_H	See the functional test circuit	100		mA
C_{off}	$V_R = -5V$ $F=1MHz$		100	pF

OPERATION WITH GATE

Symbol	Test conditions	Min.	Max.	Unit
V_G note1	$I_{GATE} = 200mA$ (for either G_n or G_p)	0.6	1.8	V
I_{GP}	$V_{Anode-cathode} = 60V$		180	mA
I_{GN}	$V_{Anode-cathode} = 60V$	80	200	mA

Note 1 : $V_G = V_{GN}$, measured between G_n and cathode
 $V_G = V_{GP}$, measured between G_p and anode

FUNCTIONAL HOLDING CURRENT (I_H) TEST CIRCUIT : GO-NO GO TEST

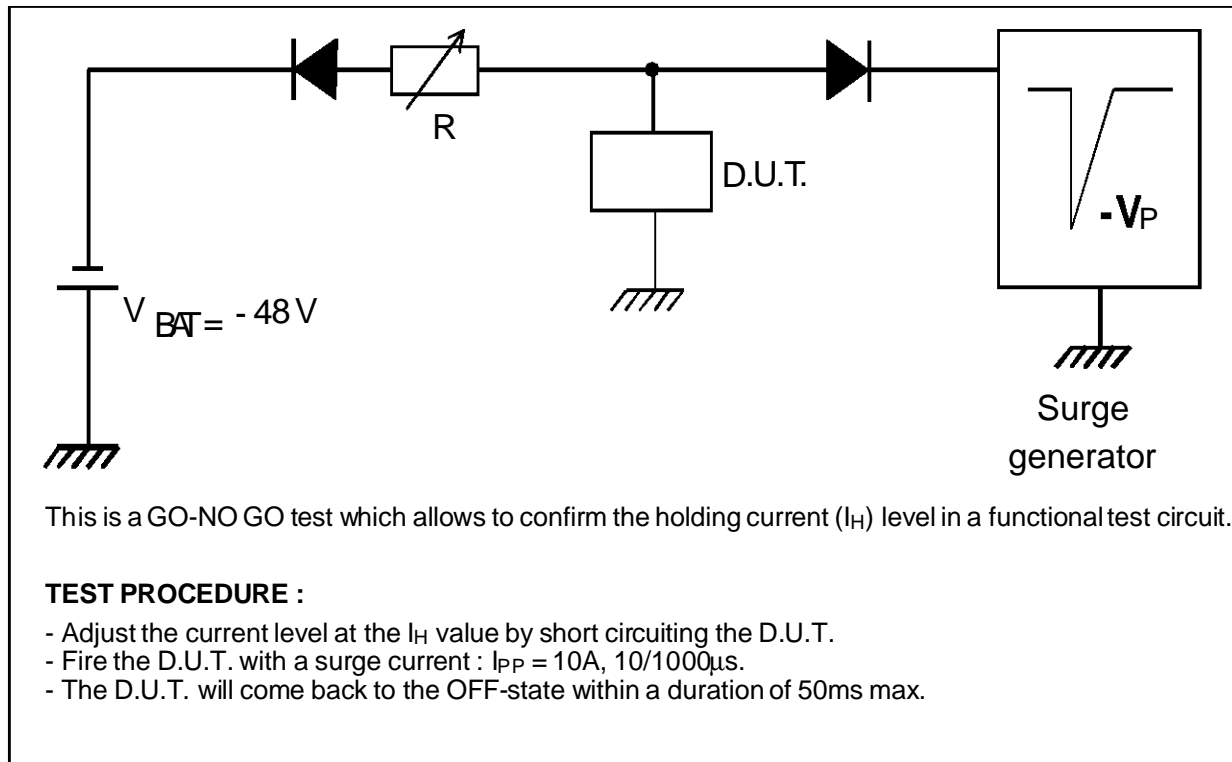


Fig. 1 : Maximum non repetitive surge peak-on-state current versus overload duration.

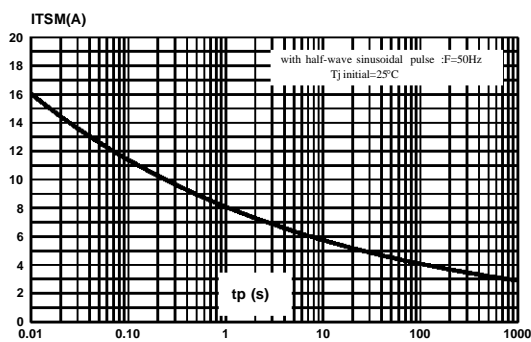
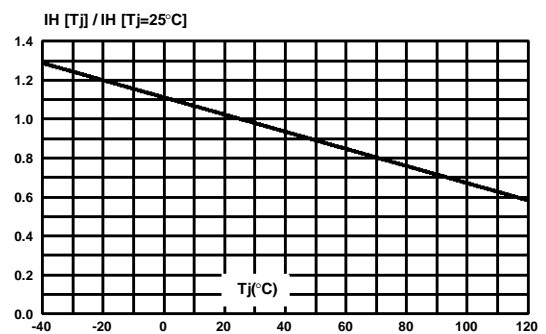
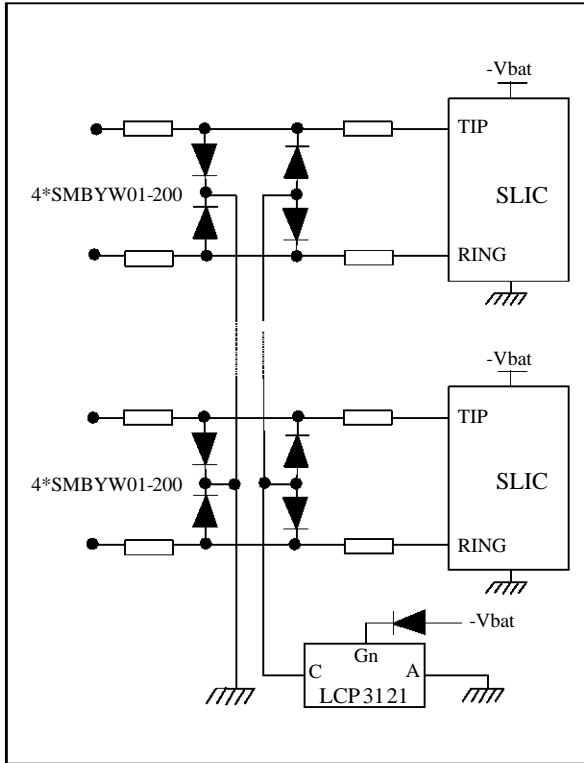


Fig. 2 : Relative variation of holding current versus junction temperature (typical values).

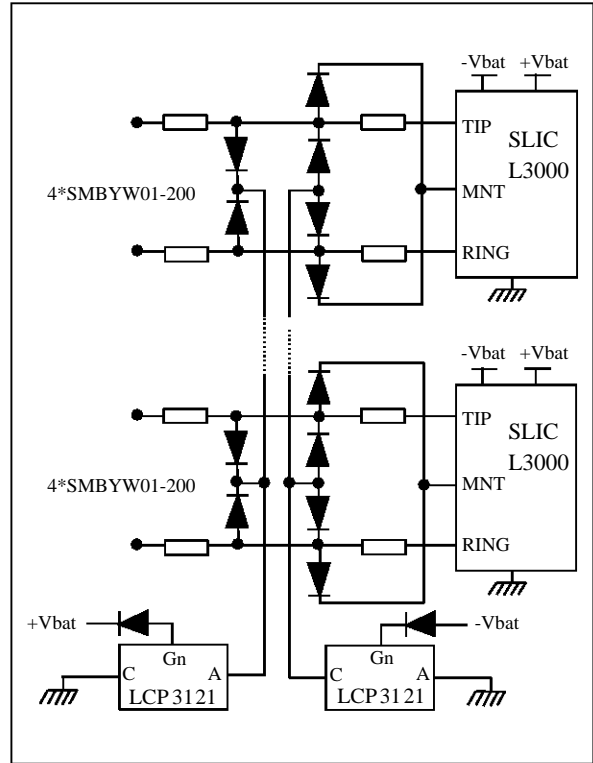


APPLICATION EXAMPLES

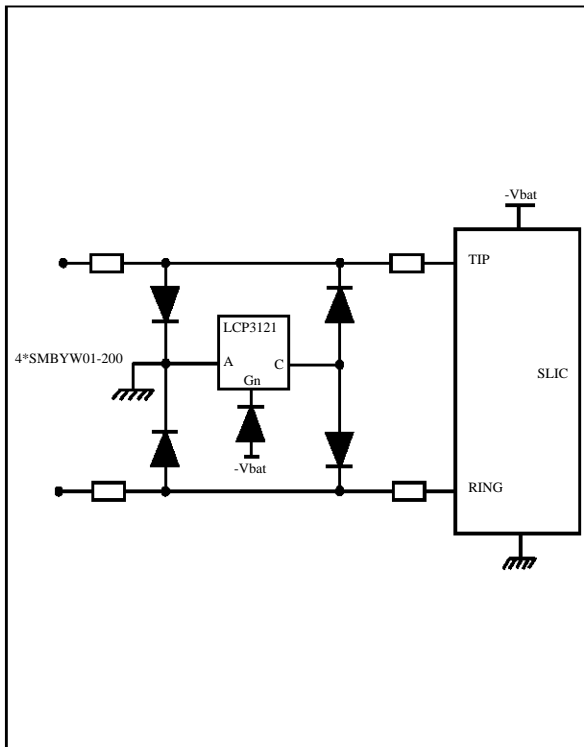
Application 1 : Common protection for SLIC without integrated ring generator



Application 2 : Common protection for SLIC with integrated ring generator



Application 3 : Typical SLIC protection



Application 4 : Protection programmed by current

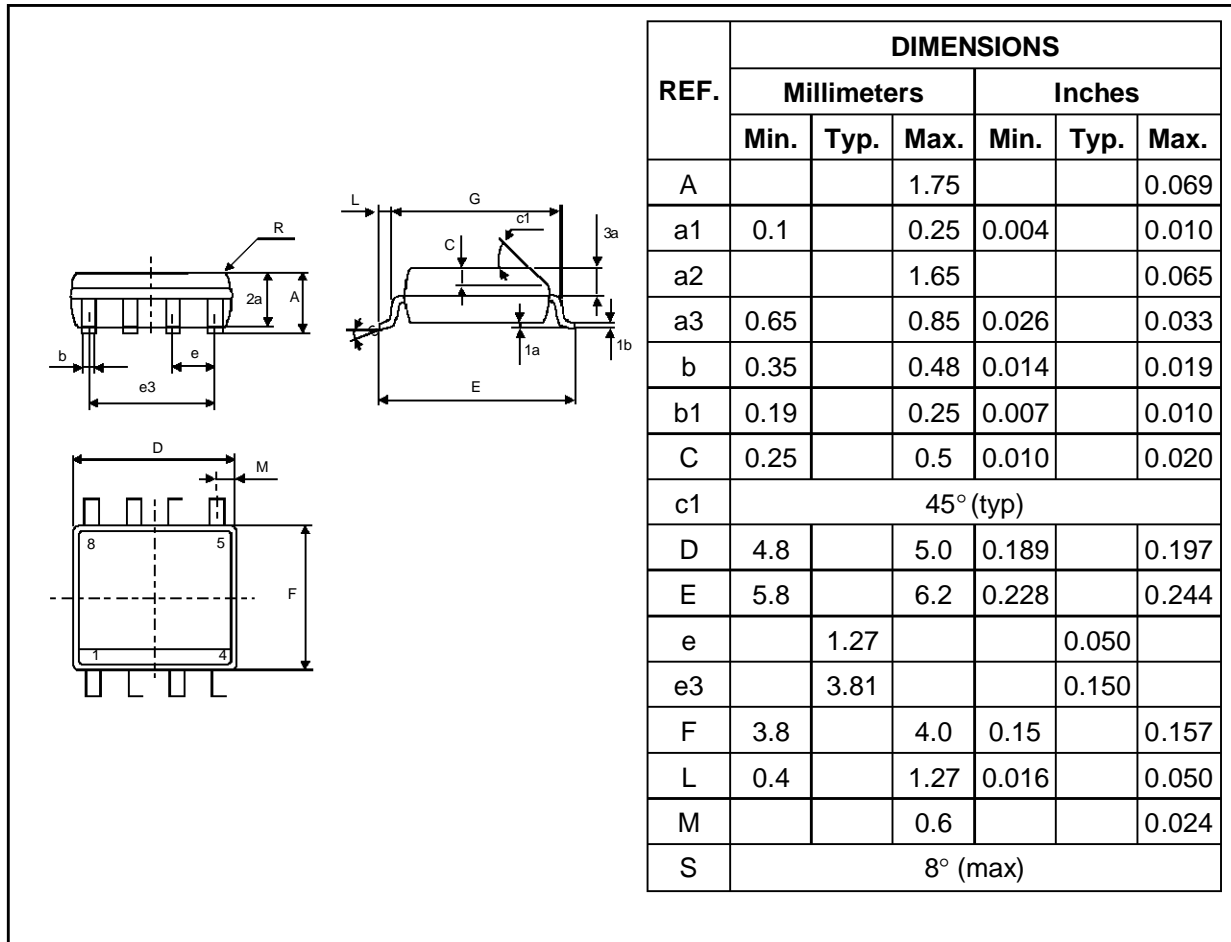
$$I_T = I_G + \frac{V_G}{R_a}$$

CURRENT TOLERANCE		
R_a Ω (+/-5%)	I_T mA min	I_T mA max
4.7	202	603
5.6	182	538
6.8	164	479
8.2	150	431
10.1	137	388
12.0	128	358

LCP3121

PACKAGE MECHANICAL DATA

SO8 Plastic



MARKING

Package	Type	Marking
SO8	LCP3121	CP3121

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